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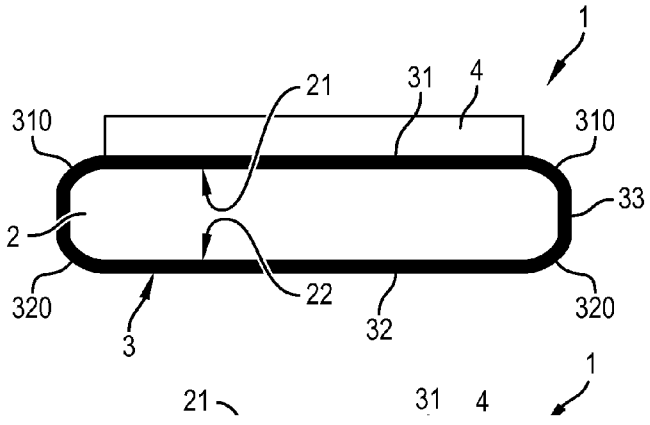
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(54) Title: A TEST METHOD ON THE SUPPORT SUBSTRATE OF A SUBSTRATE OF THE "SEMICONDUCTOR ON INSULATOR" TYPE

FIG. 1



(57) Abstract: The invention relates to a test method comprising an electrical connection contact on the support (2) of a substrate of the "semiconductor on insulator" type (1). This method is remarkable in that it comprises the steps of : a) taking a substrate (1) of the "semiconductor on insulator" type comprising a support substrate (2) entirely covered with an insulator layer (3) and an active layer (4), a portion (31) of said insulator layer (3) being buried between the active layer and the front face (21) of the support substrate (2), b) removing a portion of said insulator layer (3) which extends at the periphery of the front face (21) of the support substrate (2) and/or which extends on its rear face (22), so as to delimit at least one insulator-free accessible area (210) of the support substrate (2), while retaining at least one portion (321) of the insulator layer on the rear face, c) applying an electrical voltage to said accessible area (210), in order to make said electrical connection contact.

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